IXYS

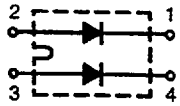
Fast Recovery Epitaxial Diodes

DSEI 2x61

I_{FAV} = 2x60 A
V_{RRM} = 600-1000 V
t_{rr} ≤ 50 ns

miniBLOC, SOT-227 B

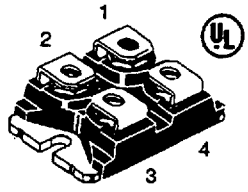
V_{RSM} V	V_{RRM} V	Type
640	600	DSEI 2x61-06B
800	800	DSEI 2x61-08B
1000	1000	DSEI 2x61-10B



Symbol	Test Conditions	Maximum Ratings (per diode)	
I_{FRMS}	$T_{VJ} = T_{VJM}$	100	A
I_{FAVM} 1)	T_C = 50°C; rectangular, δ = 0.5	60	A
I_{FRM}	t_P < 10 µs; rep. rating, pulse width limited by T_{VJM}	800	A
I_{FSM}	T_{VJ} = 45°C; t = 10 ms (50 Hz), sine	500	A
	t = 8.3 ms (60 Hz), sine	540	A
	T_{VJ} = 150°C; t = 10 ms (50 Hz), sine	450	A
	t = 8.3 ms (60 Hz), sine	480	A
$\int i^2dt$	T_{VJ} = 45°C t = 10 ms (50 Hz), sine	1150	A^2s
	t = 8.3 ms (60 Hz), sine	1200	A^2s
	T_{VJ} = 150°C; t = 10 ms (50 Hz), sine	1000	A^2s
	t = 8.3 ms (60 Hz), sine	950	A^2s
T_{VJ}		-40...+150	°C
T_{VJM}		150	°C
T_{stg}		-40...+150	°C
P_{tot}	T_C = 25°C	180	W
V_{ISOL}	50/60 Hz t = 1 min	2500	V~
	I_{ISOL} = 1 mA t = 1 s	3000	V~
M_d	Mounting torque (M4)	1.5/13	Nm/lb.in.
	Terminal connection torque (M4)	1.5/13	Nm/lb.in.
Weight		30	g

Symbol	Test Conditions	Characteristic Values (per diode) typ.	max.	
I_R	T_{VJ} = 25°C $V_R = V_{RRM}$		3	mA
I_R	T_{VJ} = 25°C V_R = 0.8 • V_{RRM}		500	µA
	T_{VJ} = 125°C V_R = 0.8 • V_{RRM}		14	mA
V_F	I_F = 60 A; T_{VJ} = 150°C		1.8	V
	T_{VJ} = 25°C		2.3	V
V_{TO}	For power-loss calculations only		1.43	V
r_F	$T_{VJ} = T_{VJM}$		6.1	mΩ
R_{thJC}			0.7	K/W
R_{thCK}			0.05	K/W
t_{rr}	I_F = 1 A; di/dt = -15 A/µs; V_R = 30 V; T_{VJ} = 25°C		50	ns
I_{RM}	V_R = 540 V; I_F = 60 A; di_F/dt = -480 A/µs	32	36	A
	L ≤ 0.05 µH; T_{VJ} = 100°C			

1) I_{FAVM} Rating includes reverse blocking losses at T_{VJM}, V_R = 0.8 • V_{RRM}, duty cycle δ = 0.5
Standards: DIN/IEC 747



E72873 (M)

Features
- International standard package miniBLOC (ISOTOP compatible)
- Isolation voltage 2500 V (RMS)
- Glass passivated chips
- Very short recovery time
- Extremely low losses at high switching frequencies
- Low I_{RM}-values
- Soft recovery behaviour

Applications
- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switched-mode power supplies
- Inductive heating and melting
- Uninterruptible power systems (UPS)
- Ultrasonic cleaners and welders

Advantages
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses
- Operating at lower temperature or space saving by reduced cooling

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DSEI 2x61, 600-1000 V

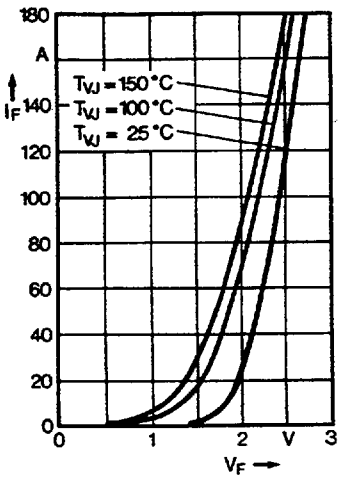


Fig. 1 Forward current versus voltage drop

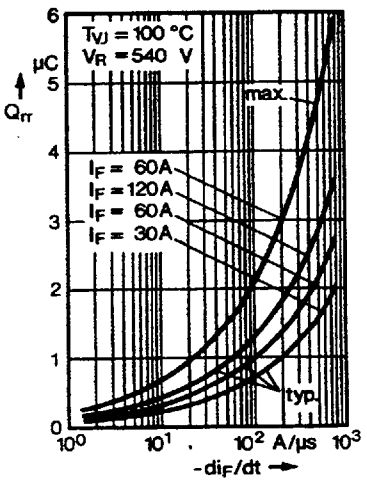


Fig. 2 Recovery charge versus $-di_F/dt$.

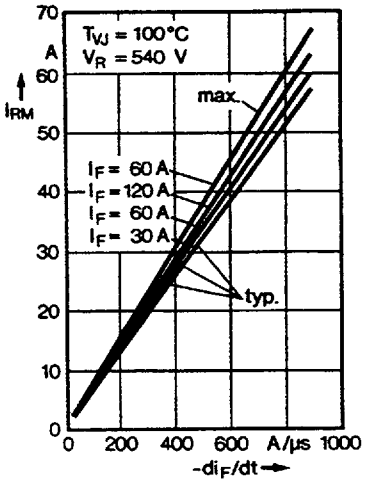


Fig. 3 Peak reverse current versus $-di_F/dt$.

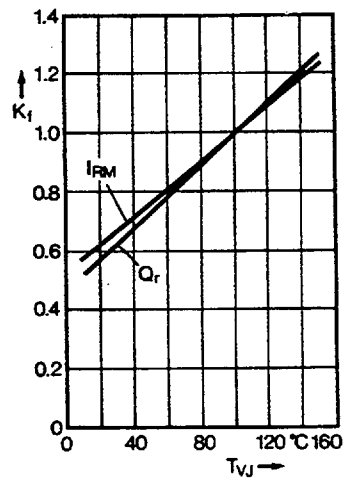


Fig. 4 Dynamic parameters versus junction temperature.

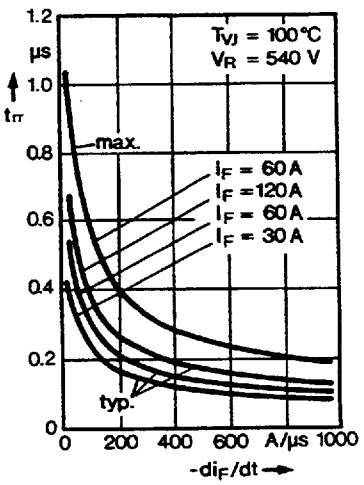


Fig. 5 Recovery time versus $-di_F/dt$.

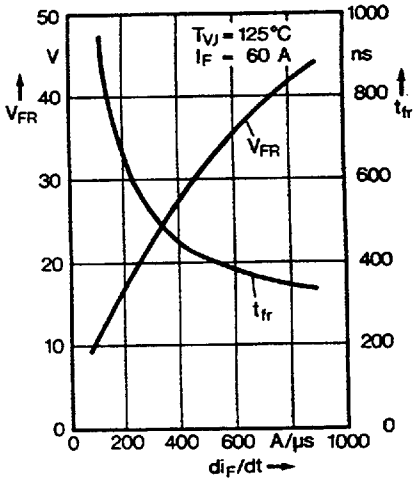


Fig. 6 Peak forward voltage versus $-di_F/dt$.

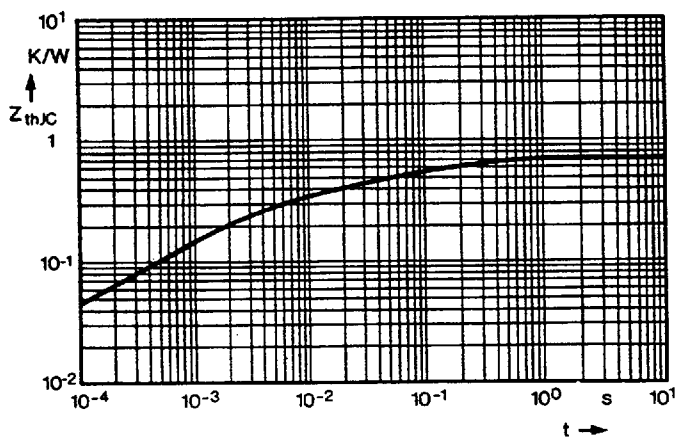
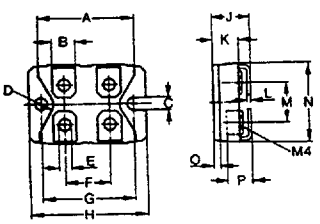


Fig. 7 Transient thermal impedance junction to case.



MINIBLOC SOT-227 B
M4 screws (4x) supplied

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	31.5	31.7	1.241	1.249
B	7.8	8.2	0.307	0.323
C	4.0	-	0.158	-
D	4.1	4.3	0.162	0.169
E	4.1	4.3	0.162	0.169
F	14.9	15.1	0.587	0.595
G	30.1	30.3	1.186	1.193
H	38.0	38.2	1.497	1.505
J	11.8	12.2	0.465	0.481
K	8.9	9.1	0.351	0.359
L	0.75	0.85	0.030	0.033
M	12.6	12.8	0.496	0.504
N	25.2	25.4	0.993	1.001
O	1.95	2.05	0.077	0.081
P	-	5.0	-	0.197

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